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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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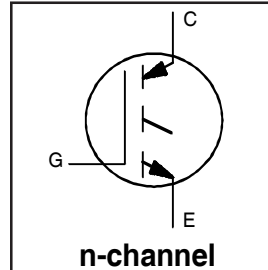
# IRG4BC10KPbF

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated  
UltraFast IGBT

## Features

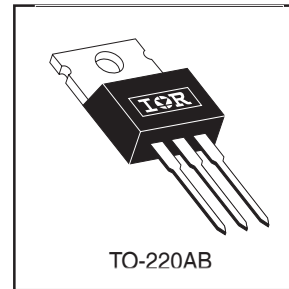
- Short Circuit Rated UltraFast: Optimized for high operating frequencies >5.0 kHz , and Short Circuit Rated to 10 $\mu$ s @ 125°C, V<sub>GE</sub> = 15V
- Generation 4 IGBT design provides higher efficiency than Generation 3
- Industry standard TO-220AB package
- Lead-Free



V <sub>CES</sub> = 600V
V <sub>CE(on)</sub> typ. = 2.39V
@ V <sub>GE</sub> = 15V, I <sub>C</sub> = 5.0A

## Benefits

- Generation 4 IGBTs offer highest efficiency available
- IGBTs optimized for specified application conditions



## Absolute Maximum Ratings

	Parameter	Max.	Units
V <sub>CES</sub>	Collector-to-Emitter Breakdown Voltage	600	V
I <sub>C</sub> @ T <sub>C</sub> = 25°C	Continuous Collector Current	9.0	A
I <sub>C</sub> @ T <sub>C</sub> = 100°C	Continuous Collector Current	5.0	
I <sub>CM</sub>	Pulsed Collector Current ①	18	
I <sub>LM</sub>	Clamped Inductive Load Current ②	18	
t <sub>sc</sub>	Short Circuit Withstand Time	10	$\mu$ s
V <sub>GE</sub>	Gate-to-Emitter Voltage	$\pm$ 20	V
E <sub>ARV</sub>	Reverse Voltage Avalanche Energy ③	34	mJ
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	38	W
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation	15	
T <sub>J</sub> T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case )	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
R <sub><math>\theta</math>JC</sub>	Junction-to-Case	—	3.3	°C/W
R <sub><math>\theta</math>CS</sub>	Case-to-Sink, Flat, Greased Surface	0.5	—	
R <sub><math>\theta</math>JA</sub>	Junction-to-Ambient, typical socket mount	—	80	
Wt	Weight	2.0 (0.07)	—	g (oz)

# IRG4BC10KPbF

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

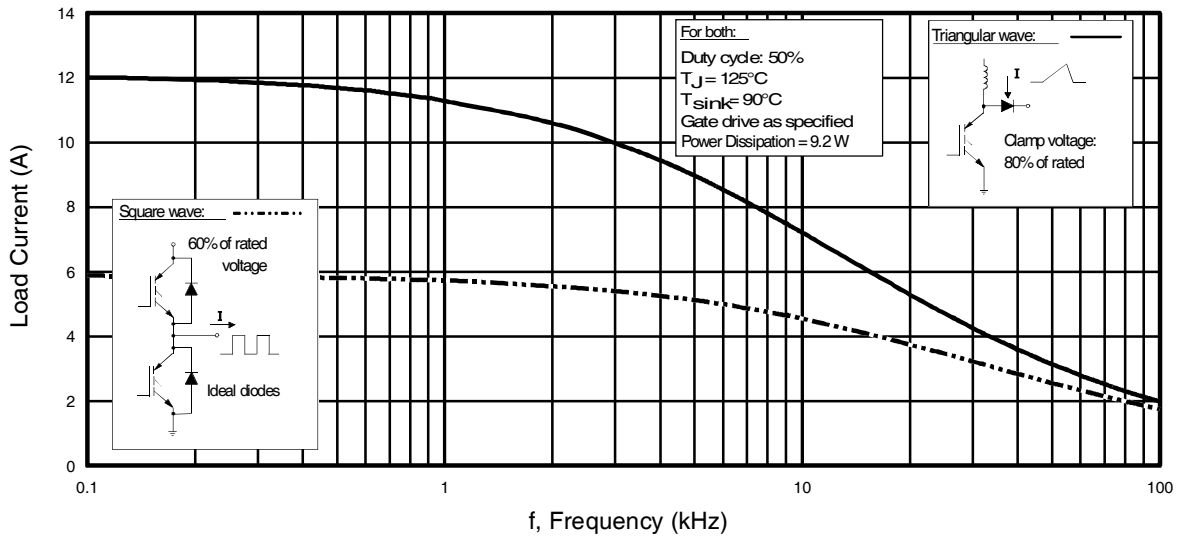
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.58	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.39	2.62	V	$I_C = 5.0A$ $I_C = 9.0A$ $I_C = 5.0A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig.2, 5
		—	3.25	—		
		—	2.63	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance ⑤	1.2	1.8	—	S	$V_{CE} = 50V, I_C = 5.0A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

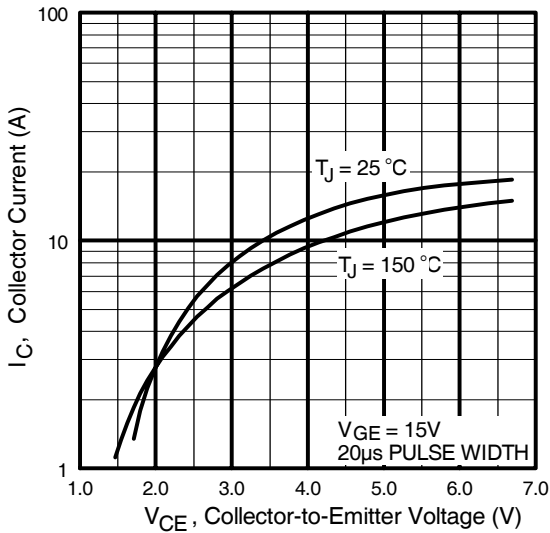
	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	19	29	nC	$I_C = 5.0A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig.8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	2.9	4.3		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	9.8	15		
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$ Energy losses include "tail" See Fig. 9,10,14
$t_r$	Rise Time	—	24	—		
$t_{d(off)}$	Turn-Off Delay Time	—	51	77		
$t_f$	Fall Time	—	190	290		
$E_{on}$	Turn-On Switching Loss	—	0.16	—	mJ	See Fig. 9,10,14
$E_{off}$	Turn-Off Switching Loss	—	0.10	—		
$E_{ts}$	Total Switching Loss	—	0.26	0.32		
$t_{sc}$	Short Circuit Withstand Time	10	—	—	$\mu s$	$V_{CC} = 400V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 100\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$T_J = 150^\circ\text{C}$ $I_C = 5.0A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 100\Omega$ Energy losses include "tail" See Fig. 10,11,14
$t_r$	Rise Time	—	27	—		
$t_{d(off)}$	Turn-Off Delay Time	—	67	—		
$t_f$	Fall Time	—	350	—		
$E_{ts}$	Total Switching Loss	—	0.47	—	mJ	
$L_E$	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	220	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{oes}$	Output Capacitance	—	29	—		
$C_{res}$	Reverse Transfer Capacitance	—	7.5	—		

### Notes:

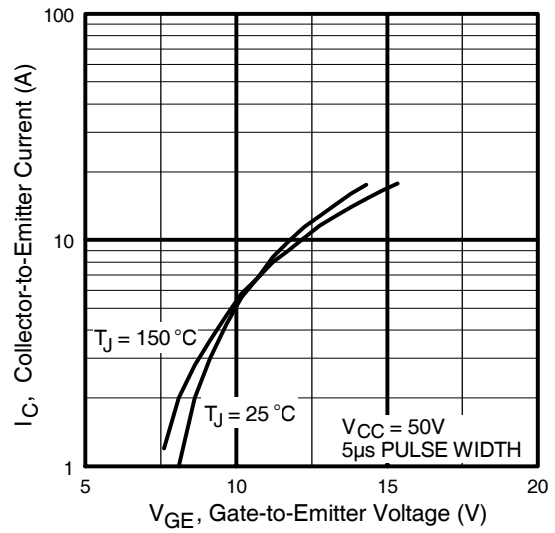
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 10\mu H$ ,  $R_G = 100\Omega$ , (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.



**Fig. 1 - Typical Load Current vs. Frequency**  
 (Load Current =  $I_{\text{RMS}}$  of fundamental)

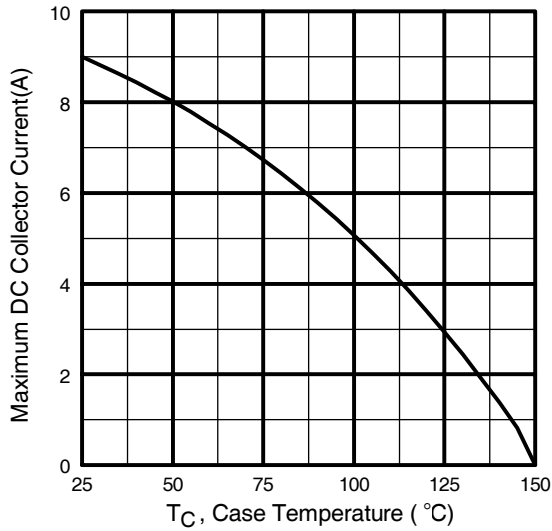


**Fig. 2 - Typical Output Characteristics**

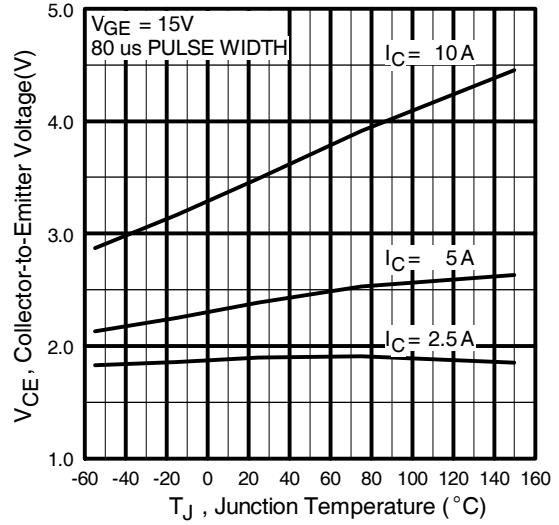


**Fig. 3 - Typical Transfer Characteristics**

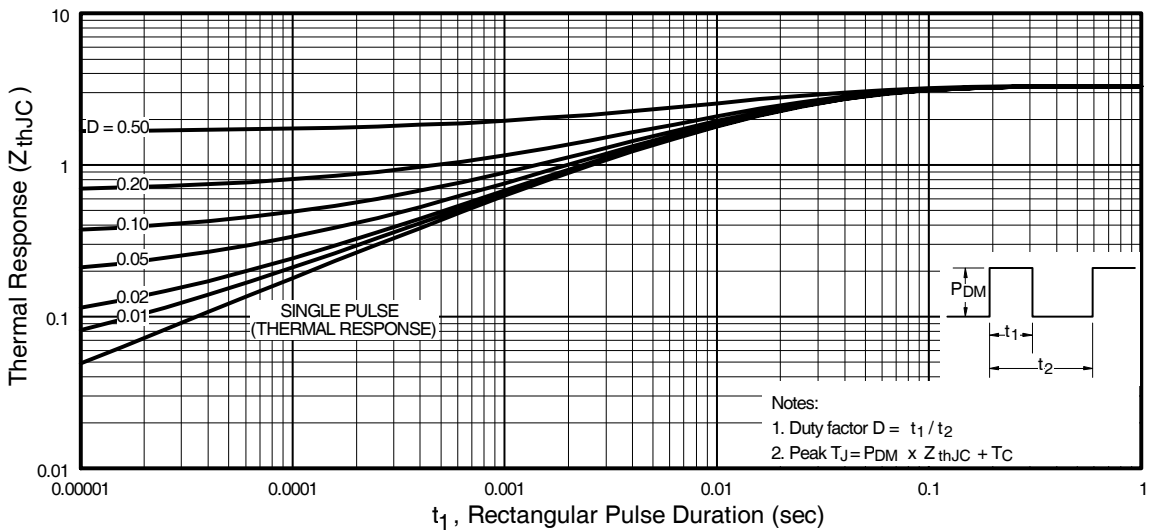
# IRG4BC10KPbF



**Fig. 4** - Maximum Collector Current vs. Case Temperature

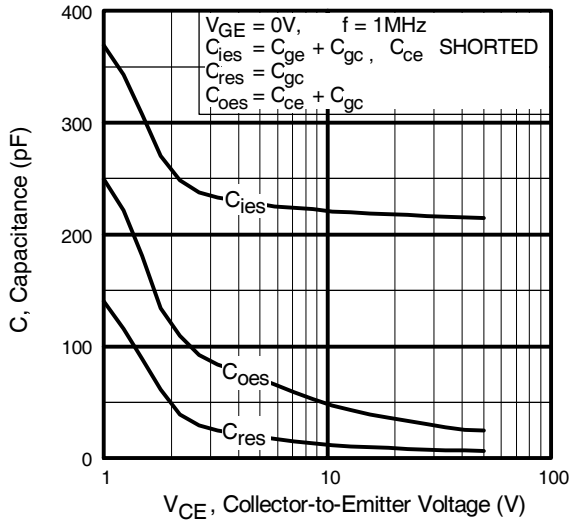


**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature

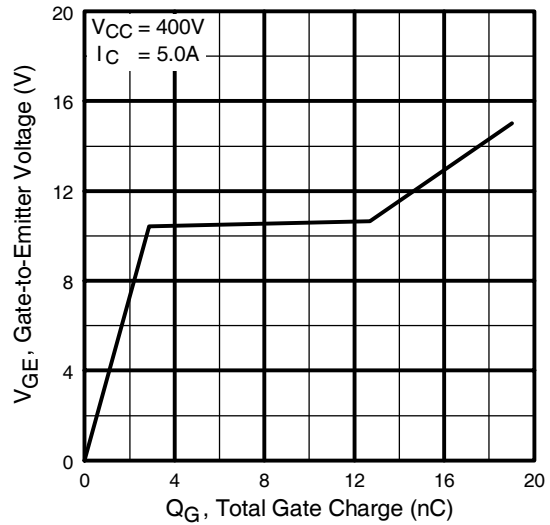


**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case

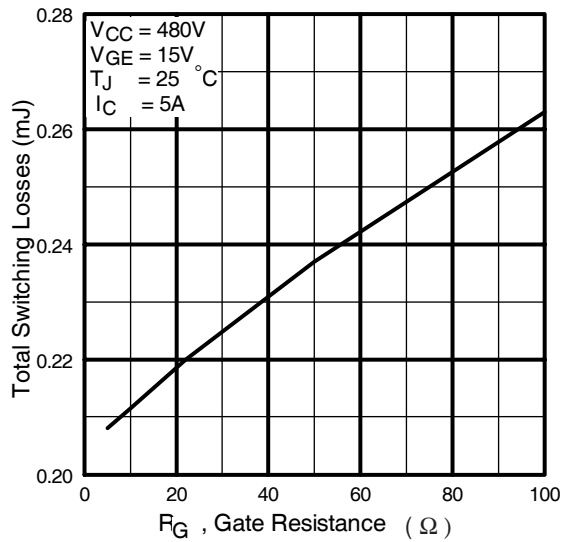
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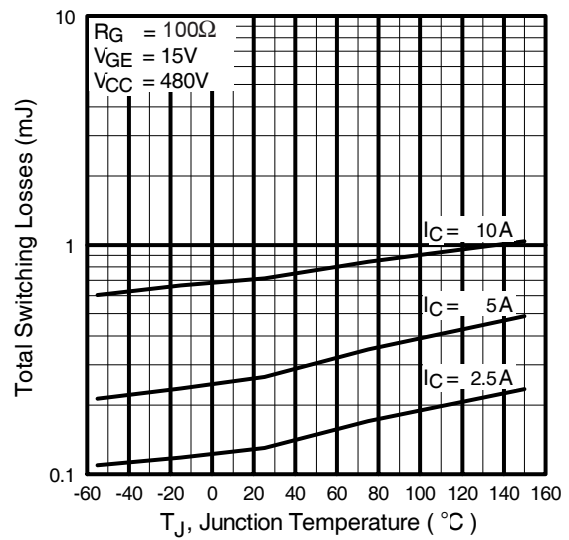
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage

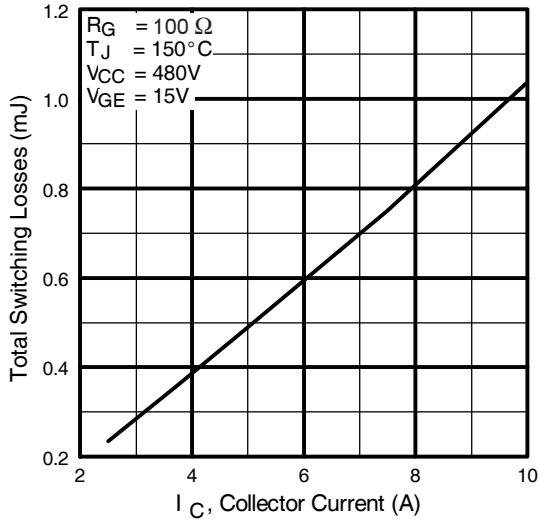


**Fig. 9** - Typical Switching Losses vs. Gate Resistance

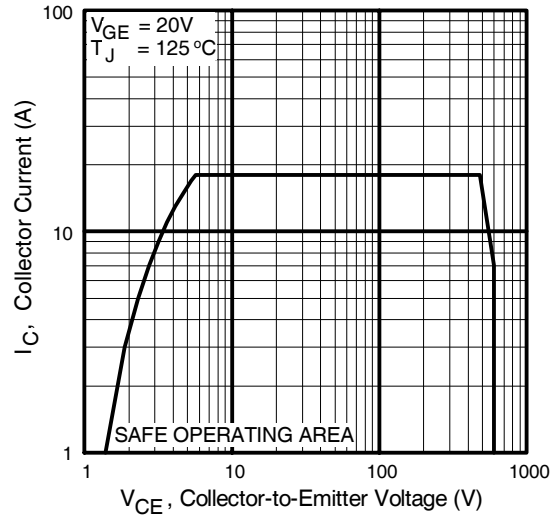


**Fig. 10** - Typical Switching Losses vs. Junction Temperature

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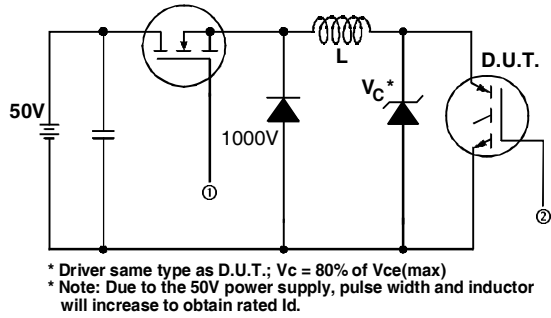


**Fig. 11** - Typical Switching Losses vs. Collector Current

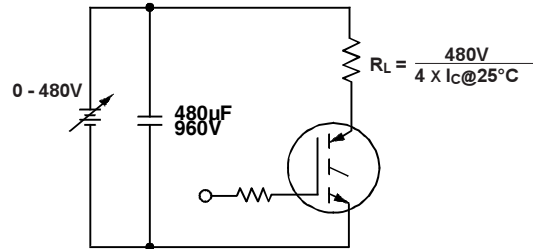


**Fig. 12** - Turn-Off SOA

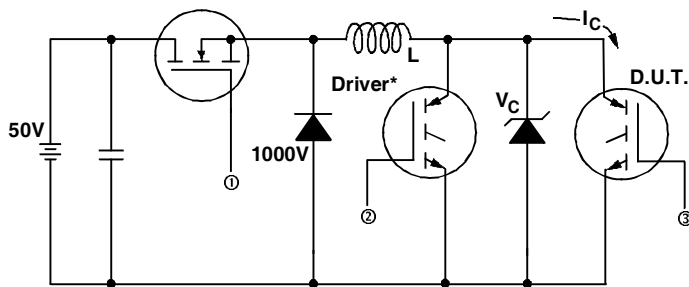
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**Fig. 13a** - Clamped Inductive Load Test Circuit

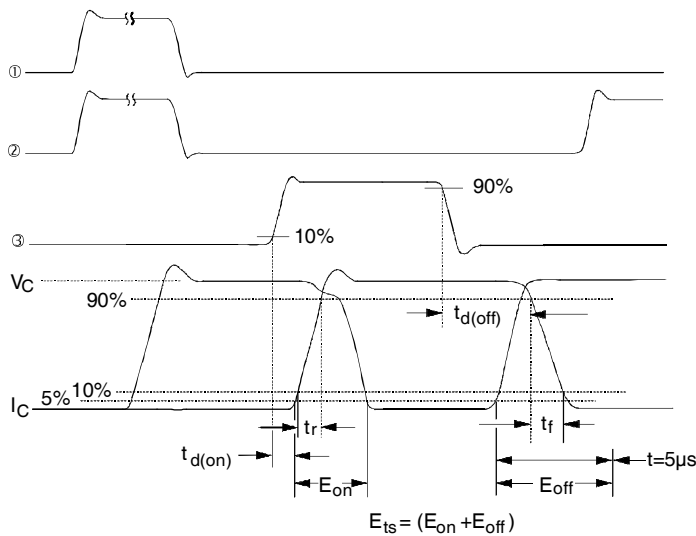


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T.,  $V_C = 480V$



**Fig. 14b** - Switching Loss Waveforms

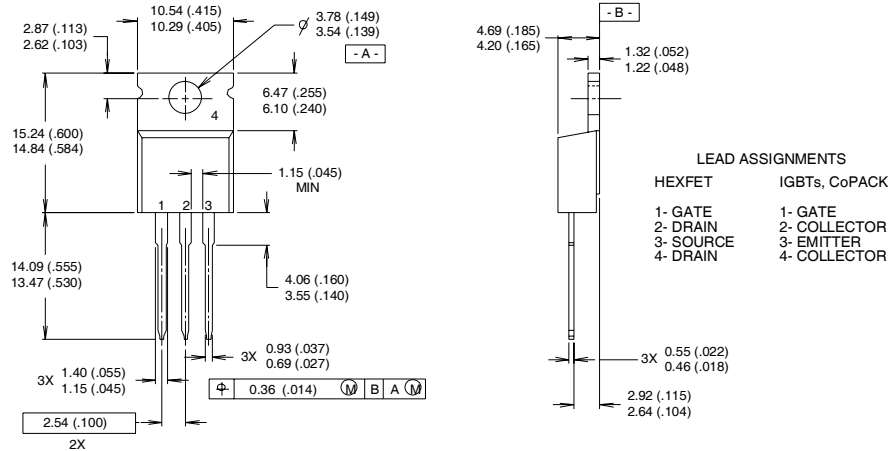


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## TO-220AB Package Outline

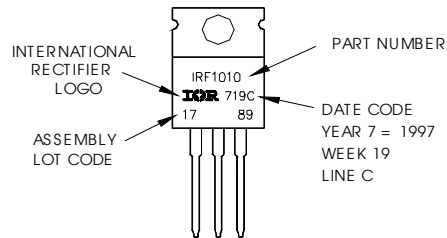
Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
  - 2 CONTROLLING DIMENSION : INCH
  - 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
  - 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line  
 position indicates "Lead-Free"



Data and specifications subject to change without notice.



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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>